

N-Channel Enhancement-Mode MOSFET Transistors

Zener Gate Protected

Product Summary

Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max (Ω)	$V_{GS(th)}$ (V)	I_D (A)
VN0610L	60	5 @ $V_{GS} = 10$ V	0.8 to 2.5	0.27
VN10KE		5 @ $V_{GS} = 10$ V	0.8 to 2.5	0.17
VN10KM		5 @ $V_{GS} = 10$ V	0.8 to 2.5	0.31
VN10KT		5 @ $V_{GS} = 10$ V	0.8 to 2.5	0.31
VN2222L		7.5 @ $V_{GS} = 10$ V	0.6 to 2.5	0.23

Features

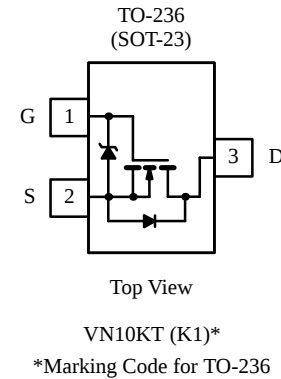
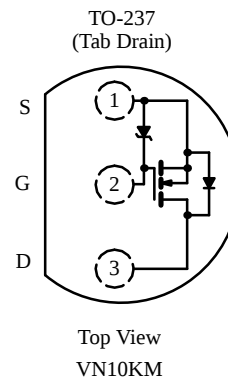
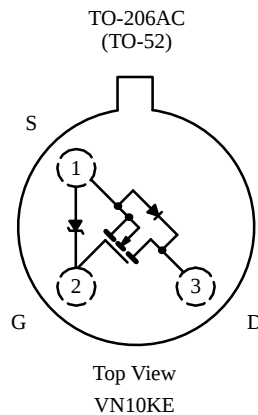
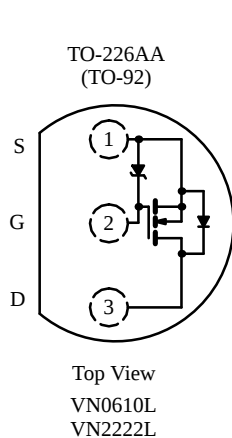
- Zener Diode Input Protected
- Low On-Resistance: 3 Ω
- Ultralow Threshold: 1.2 V
- Low Input Capacitance: 38 pF
- Low Input and Output Leakage

Benefits

- Extra ESD Protection
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed, Easily Driven
- Low Error Voltage

Applications

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays
- Inductive Load Drivers



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	VN2222L VN0610L	VN10KE	VN10KM VN10KT	Unit
Drain-Source Voltage	V_{DS}	60	60	60	V
Gate-Source Voltage	V_{GS}	15/-0.3	15/-0.3	15/-0.3	V
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_A = 25^\circ\text{C}$ 0.27	0.17	0.31	A
		$T_A = 100^\circ\text{C}$ 0.17	0.11	0.20	
Pulsed Drain Current ^a	I_{DM}	1	1	1	A
Power Dissipation	P_D	$T_A = 25^\circ\text{C}$ 0.8	0.3	1	W
		$T_A = 100^\circ\text{C}$ 0.32	0.12	0.4	
Maximum Junction-to-Ambient	R_{thJA}	156	400	125	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150			$^\circ\text{C}$

Notes

a. Pulse width limited by maximum junction temperature.

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70213.

Specifications^a

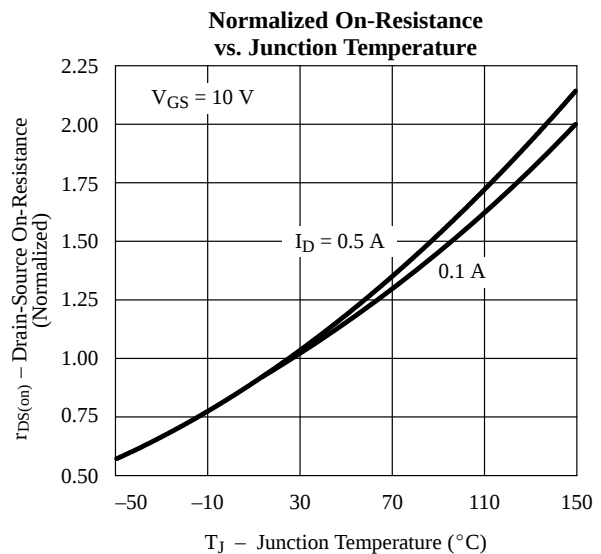
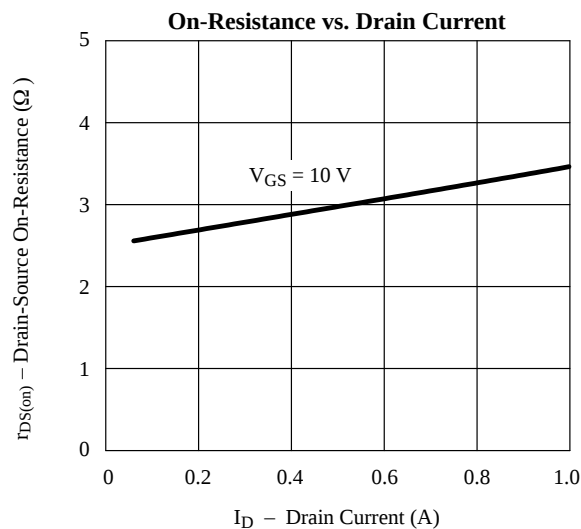
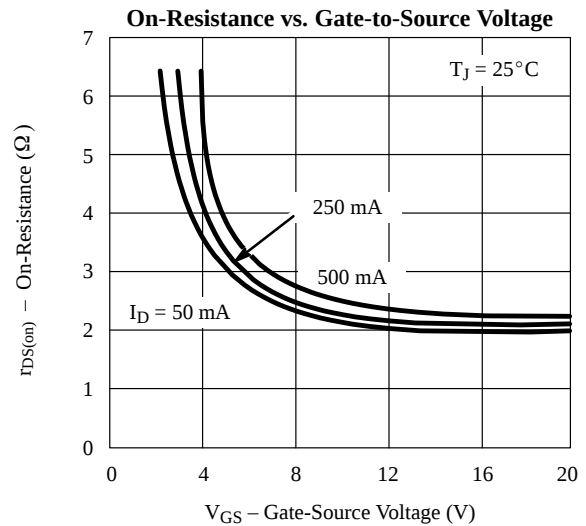
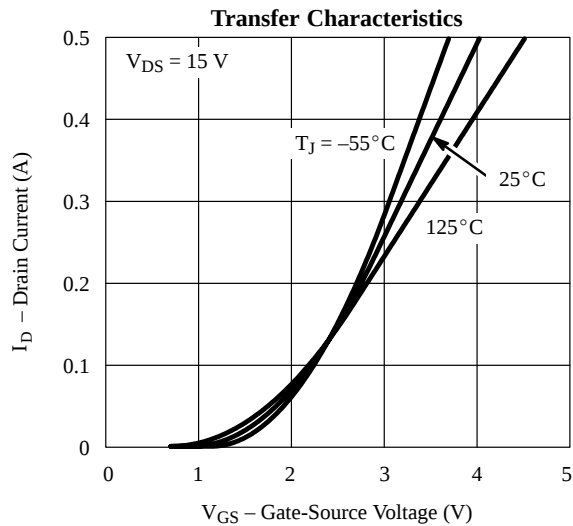
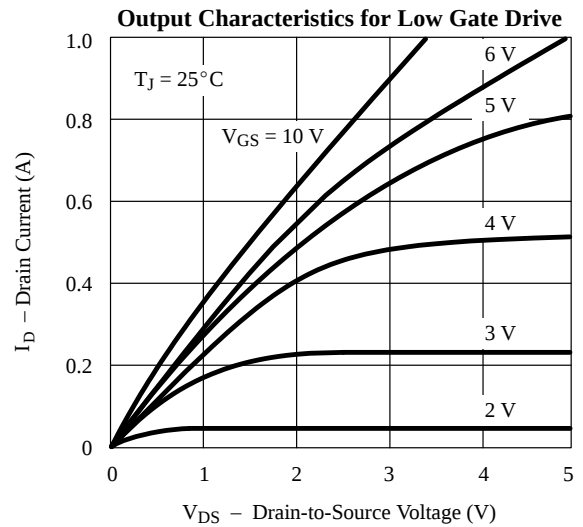
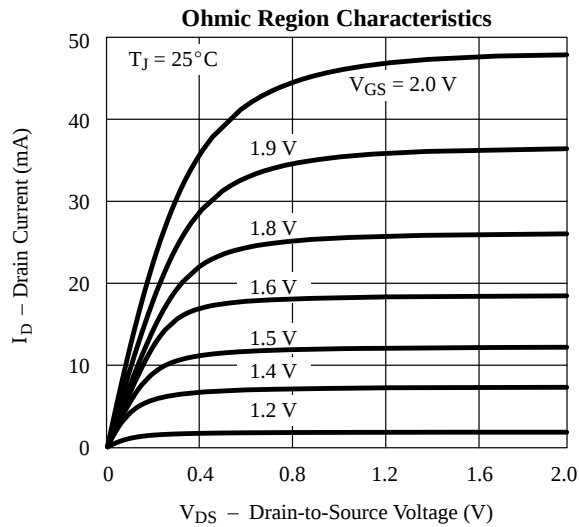
Parameter	Symbol	Test Conditions	Typ ^b	Limits				Unit
				VN0610L VN10KE VN10KM VN10KT		VN2222L		
				Min	Max	Min	Max	
Static								
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 100 μA	120	60		60		V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1 mA	1.2	0.8	2.5	0.6	2.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = 15 V	1		100		100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48 V, V _{GS} = 0 V			10		10	μA
		T _J = 125°C			500		500	
On-State Drain Current ^c	I _{D(on)}	V _{DS} = 10 V, V _{GS} = 10 V	1	0.75		0.75		A
Drain-Source On-Resistance ^c	r _{DS(on)}	V _{GS} = 5 V, I _D = 0.2 A	4		7.5		7.5	Ω
		V _{GS} = 10 V, I _D = 0.5 A	3		5		7.5	
		T _J = 125°C	5.6		9		13.5	
Forward Transconductance ^c	g _{fs}	V _{DS} = 10 V, I _D = 0.5 A	300	100		100		mS
Common Source Output Conductance ^c	g _{os}	V _{DS} = 7.5 V, I _D = 0.05 A	0.2					
Dynamic								
Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	38		60		60	pF
Output Capacitance	C _{oss}		16		25		25	
Reverse Transfer Capacitance	C _{rss}		2		5		5	
Switching ^d								
Turn-On Time	t _{ON}	V _{DD} = 15 V, R _L = 23 Ω I _D ≅ 0.6 A, V _{GEN} = 10 V R _G = 25 Ω	7		10		10	ns
Turn-Off Time	t _{OFF}		9		10		10	

Notes

- a. $T_A = 25^\circ\text{C}$ unless otherwise noted.
 b. For DESIGN AID ONLY, not subject to production testing.
 c. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
 d. Switching time is essentially independent of operating temperature.

VNPD06

Typical Characteristics (25°C Unless Otherwise Noted)



Typical Characteristics (25°C Unless Otherwise Noted) (Cont'd)

